

Solid DBC Modules

Rev.1.3 Oct.20 2023

DBC070C/16KQ

Description

- 1) Components adopt vacuum welding to well control void and rated voltage up to 1600V.
- 2) A package of two inverse parallel SCRs.
- **3)** Thyristor chips are welding on the ceramic copper clad laminate, products with high electricity ability, excellent heat dissipation ability.

Typical Application

Constant temperature system, CNC machine, remote control system, lighting control, power compensation and so on.

Absolute Maximum Ratings (Packaged into modules, unless otherwise specified, T_{CASE}=25°C)

Parameter	Test Conditions	Symbol	Values	Unit
Operating junction temperature range		TJ	-40~+125	°C
Repetitive peak off-state voltage	T J =25 ℃	Vdrm	1600	V
Repetitive peak reverse voltage	T J =25 ℃	VRRM	1600	V
Non-repetitive peak off-state voltage	T J =25 ℃	V _{DSM}	1700	V
Non-repetitive peak reverse voltage	T J =25 ℃	V _{RSM}	1700	V
Average on-state current	Tc =80 ℃	I _{T(AV)}	70	А
RMS on-state current	Tc =80 ℃	I _{T(RMS)}	110	А
Non-repetitive surge peak on-state current	t _P =10ms	I _{TSM}	1400	A
l ² t value for fusing	t _P =10ms	l ² t	11250	A ² s
Critical rate of rise of on-state current	IG=2×IGT	di/dt	150	A/µs

Electrical Characteristics (Packaged into modules, unless otherwise specified, T_{CASE}=25°C)

Parameter	Test Conditions	Symbol	Values	Unit
Peak on-state voltage	I⊤м=210A,t⊵=380µs	Vтм	≤1.8	V
	V _D =V _{DRM}			
Repetitive peak off-state current	Tc =25 ℃	IDRM1	≤50	μA
	Tc =125 ℃	IDRM2	≤10	mA



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	V _R =V _{RRM}			
Repetitive peak reverse current	Tc =25 ℃	IRRM1	≤50	μA
	Tc=125℃	IRRM2	≤10	mA
Triggering gate current	$V_D=12V R_L=30\Omega$	lgт	10-80	mA
Latching current	Ig=1.2 Igт	L	≤200	mA
Holding current	IT=1A	Ін	≤150	mA
Triggering gate voltage	V_D =12V R _L =30 Ω	V _{GT}	≤2	V
Non triggering gate voltage	V D=V DRM TJ =125 ℃	V_{GD}	≥0.25	V
Critical rate of rise of voltage	V _D =2/3V _{DRM} T _J =125℃ Gate Open	dv/dt	≥1000	V/µs

Mechanical Characteristics

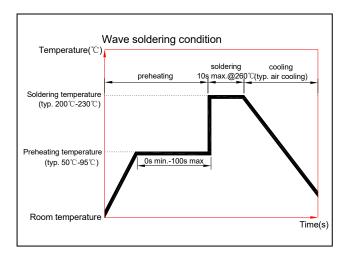
Chip size	9.8r	nm×9	.8mm						
Module size	29.7	7mm×	18.2n	nm					
Terminal height	19.2	2mm							
Solder composition and melting point of DBC			ompos oint>2		Pb92.	5%Sn	5%Ag	2.5%;	
		Dimensions							
		Ref	N	Millimeters			Inches		
			Min	Тур	Max	Min	Тур	Max	
		А	3.7	4.0	4.3	0.146	0.157	0.169	
		В	10.3	10.8	11.3	0.406	0.425	0.445	
A2		С	3.7	4.0	4.3	0.146	0.157	0.169	
		D E	0.2	0.5	0.8 19.2	0.008	0.020	0.031	
		F			6.2			0.244	
		G	0.4	0.9	1.4	0.016	0.035	0.055	
G2		H	3.9	4.4	4.9	0.154	0.173		
		1			6.0			0.236	
		J	29.4	29.7	30.0	1.157	1.169	1.181	
		K	17.9	18.2	18.5	0.705	0.717	0.728	
DBC070C/16KQ									
A2(K1) G1	G	2 K2	(A1)						
SCR2 SCR1									
symbol									



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Soldering Process Requirements

a. Hand soldering iron welding				
Soldering temperature	≤260 °C			
Soldering time	≤10s			
b. Wave soldering (see figure at right)				
Preheating temperature	≤125 ℃			
Preheating time	≤100s			
Soldering temperature	≤260 °C			
Soldering time	≤10s			



Working Conditions

1) No severe mechanical shock as impact and drop off in the process of transportation, storage and working of product.

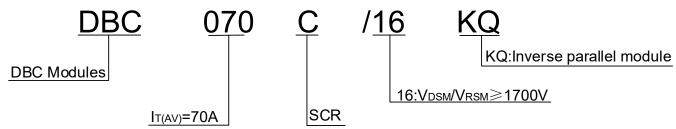
2) Storage conditions

Temperature: 5~40°C

Relative humidity: ≤45%

Storage time: 3 days for the open package; 3 months for the closed package

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